Silicon PNP Power Transistors 2SA1327

DESCRIPTION

·With TO-220Fa package
·Low collector saturation voltage
·High current capacity

APPLICATIONS

·Strobe flash applications
·Audio power amplifier applications

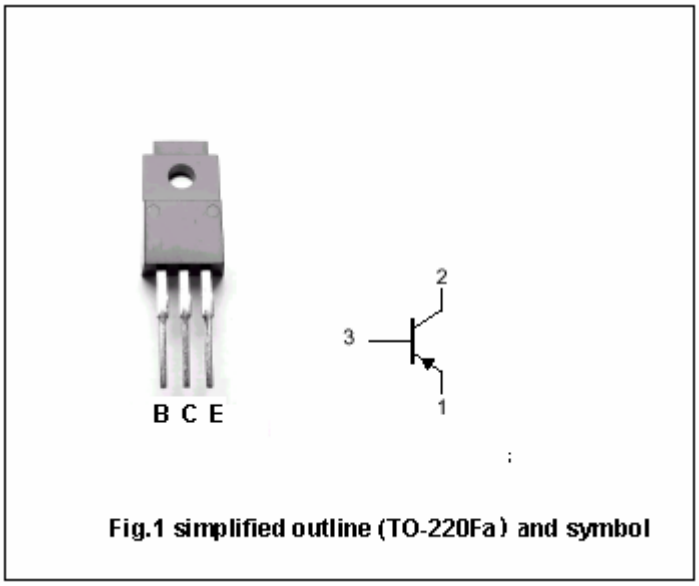

Fig.1 simplified outline (TO-220Fa) and symbol

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector
3	Base

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	-50	V
V_{CEO}	Collector-emitter voltage	Open base	-20	V
V_{EBO}	Emitter-base voltage	Open collector	-8	V
I_C	Collector current		-10	A
I_{CM}	Collector current-peak		-20	A
I_B	Base current		-2	A
P_C	Collector power dissipation	T_C=25□	20	W
		T_a=25□	2	
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=-10mA , I_B=0	-20			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=-8A; I_B=-0.4A			-0.5	V
V_{BE}	Base-emitter on voltage	I_C=-8A ; V_{CE}=-2V			-1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=-50V;I_E=0			-1.0	μA
I_{EBO}	Emitter cut-off current	V_{EB}=-8V; I_C=0			-1.0	μA
h_{FE-1}	DC current gain	I_C=-1A ; V_{CE}=-2V	100		320	
h_{FE-2}	DC current gain	I_C=-8A ; V_{CE}=-2V	70			
C_{OB}	Output capacitance	I_E=0 ; V_{CB}=-10V; f=1MHz		400		pF
f_T	Transition frequency	I_C=-1A ; V_{CE}=-2V		45		MHz

◆ **h_{FE-1} Classifications**

O	Y
100-200	160-320

PACKAGE OUTLINE

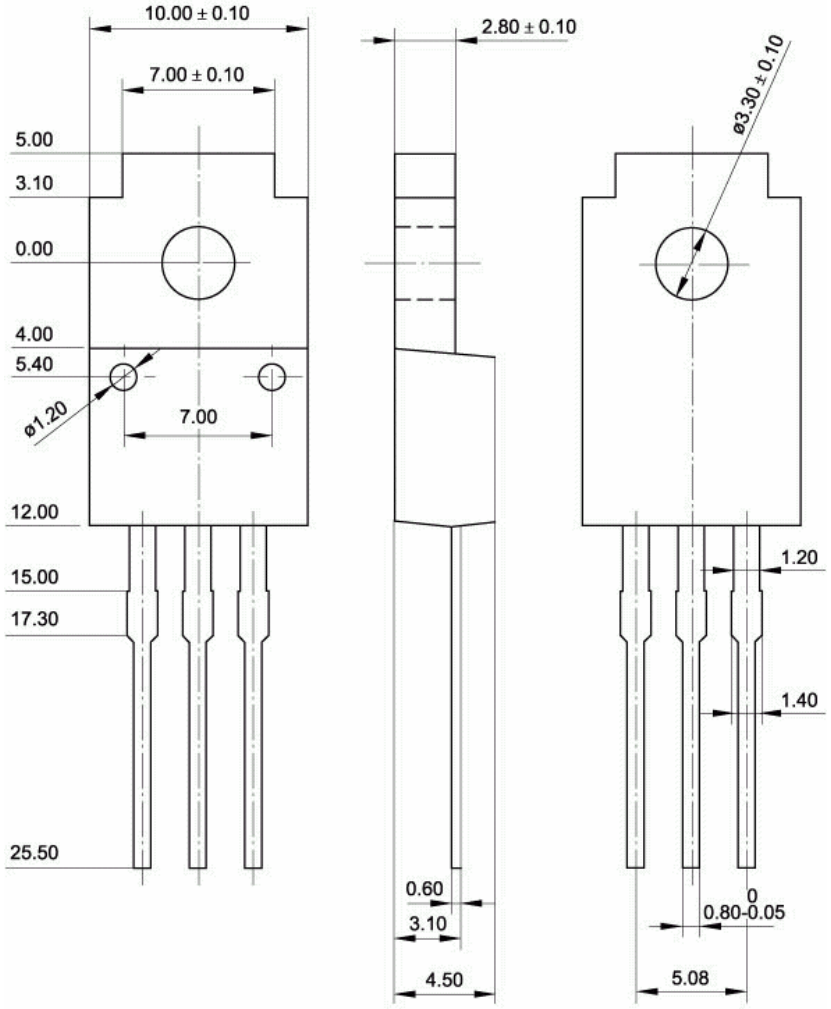

Fig.2 Outline dimensions (unindicated tolerance:±0.15 mm)

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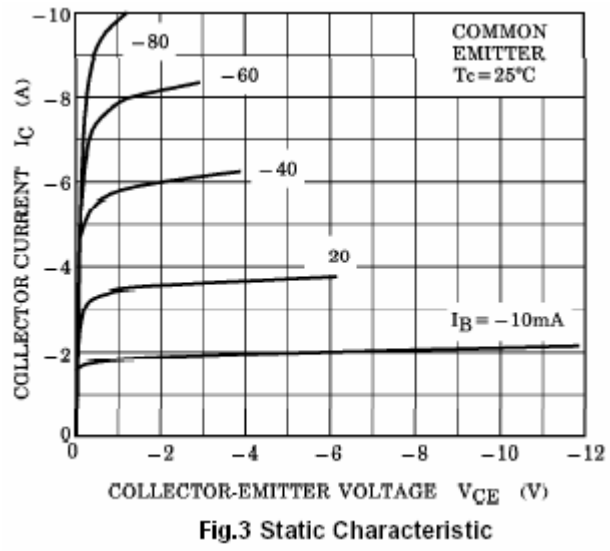

Fig.3 Static Characteristic

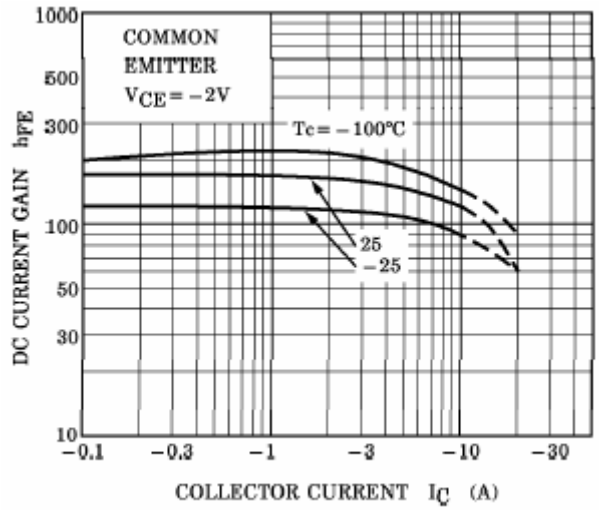

Fig.4 DC current Gain

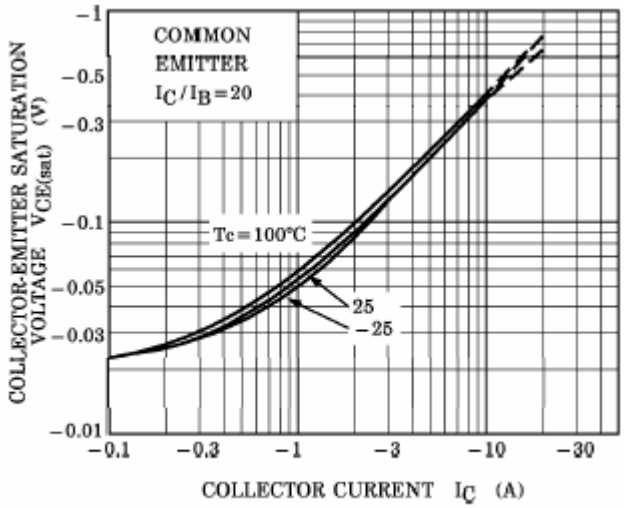

Fig.5 Collector-Emitter Saturation Voltage

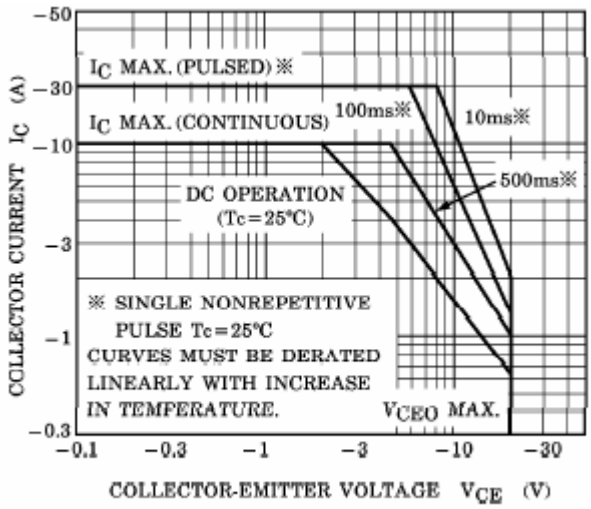

Fig.6 Safe Operating Area